

SN54ABT126, SN74ABT126 QUADRUPLE BUS BUFFER GATES WITH 3-STATE OUTPUTS

SCBS183D – FEBRUARY 1991 – REVISED JANUARY 1999

- State-of-the-Art **EPIC-IITM** BiCMOS Design Significantly Reduces Power Dissipation
- Typical V_{OLP} (Output Ground Bounce) <1 V at $V_{CC} = 5$ V, $T_A = 25^\circ\text{C}$
- High-Impedance State During Power Up and Power Down
- High-Drive Outputs ($-32\text{-mA } I_{OH}$, $64\text{-mA } I_{OL}$)
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model ($C = 200$ pF, $R = 0$)
- Package Options Include Plastic Small-Outline (D) and Shrink Small-Outline (DB) Packages, Ceramic Chip Carriers (FK), and Plastic (N) and Ceramic (J) DIPs

description

The 'ABT126 bus buffer gates feature independent line drivers with 3-state outputs. Each output is disabled when the associated output-enable (OE) input is low.

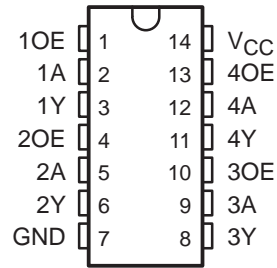
When V_{CC} is between 0 and 2.1 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 2.1 V, OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

The SN54ABT126 is characterized for operation over the full military temperature range of -55°C to 125°C . The SN74ABT126 is characterized for operation from -40°C to 85°C .

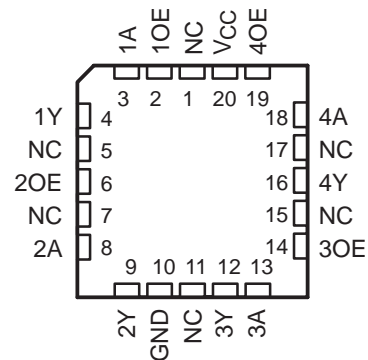
FUNCTION TABLE
(each buffer)

INPUTS		OUTPUT Y
OE	A	
H	H	H
H	L	L
L	X	Z

SN54ABT126 . . . J PACKAGE
SN74ABT126 . . . D, DB, OR N PACKAGE
(TOP VIEW)



SN54ABT126 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

EPIC-II^B is a trademark of Texas Instruments Incorporated.

UNLESS OTHERWISE NOTED this document contains PRODUCTION DATA information current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



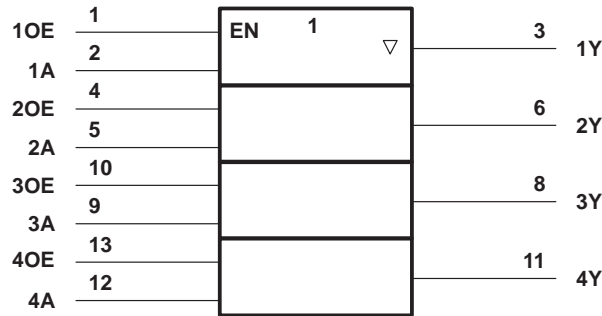
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

Copyright © 1999, Texas Instruments Incorporated

SN54ABT126, SN74ABT126
QUADRUPLE BUS BUFFER GATES
WITH 3-STATE OUTPUTS

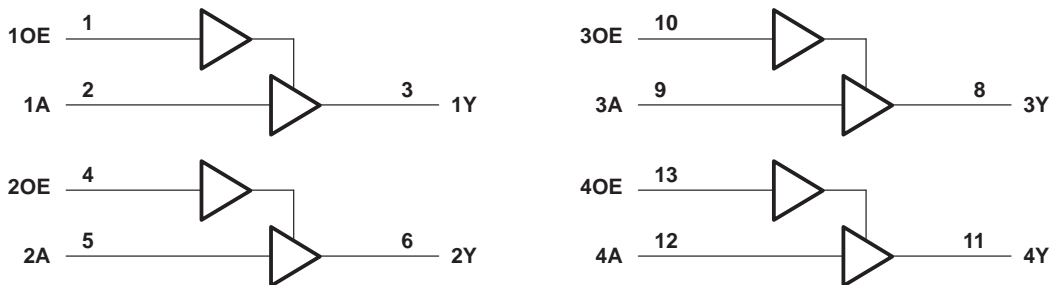
SCBS183D – FEBRUARY 1991 – REVISED JANUARY 1999

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the D, DB, J, and N packages.

logic diagram (positive logic)



Pin numbers shown are for the D, DB, J, and N packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V_{CC}	–0.5 V to 7 V
Input voltage range, V_I (see Note 1)	–0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O	–0.5 V to 5.5 V
Current into any output in the low state, I_O : SN54ABT126	96 mA
SN74ABT126	128 mA
Input clamp current, I_{IK} ($V_I < 0$)	–18 mA
Output clamp current, I_{OK} ($V_O < 0$)	–50 mA
Package thermal impedance, θ_{JA} (see Note 2): D package	127°C/W
DB package	158°C/W
N package	78°C/W
Storage temperature range, T_{stg}	–65°C to 150°C

‡ Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stressratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The package thermal impedance is calculated in accordance with JESD 51, except for through-hole packages, which use a trace length of zero.

SN54ABT126, SN74ABT126 QUADRUPLE BUS BUFFER GATES WITH 3-STATE OUTPUTS

SCBS183D – FEBRUARY 1991 – REVISED JANUARY 1999

recommended operating conditions (see Note 3)

		SN54ABT126		SN74ABT126		UNIT
		MIN	MAX	MIN	MAX	
V _{CC}	Supply voltage	4.5	5.5	4.5	5.5	V
V _{IH}	High-level input voltage	2		2		V
V _{IL}	Low-level input voltage		0.8		0.8	V
V _I	Input voltage	0	V _{CC}	0	V _{CC}	V
I _{OH}	High-level output current		–24		–32	mA
I _{OL}	Low-level output current		48		64	mA
Δt/Δv	Input transition rise or fall rate		10		10	ns/V
Δt/ΔV _{CC}	Power-up ramp rate		200		200	μs/V
T _A	Operating free-air temperature	–55	125	–40	85	°C

NOTE 3: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T _A = 25°C			SN54ABT126		SN74ABT126		UNIT
		MIN	TYP†	MAX	MIN	MAX	MIN	MAX	
V _{IK}	V _{CC} = 4.5 V, I _I = –18 mA			–1.2		–1.2		–1.2	V
V _{OH}	V _{CC} = 4.5 V, I _{OH} = –3 mA	2.5			2.5		2.5		V
	V _{CC} = 5 V, I _{OH} = –3 mA	3			3		3		
	V _{CC} = 4.5 V, I _{OH} = –24 mA	2			2				
		2*					2		
V _{OL}	V _{CC} = 4.5 V, I _{OL} = 48 mA			0.55		0.55			V
				0.55*				0.55	
V _{hys}			100						mV
I _I	V _{CC} = 0 to 5.5 V, V _I = V _{CC} or GND			±1		±1		±1	μA
I _{OZPU}	V _{CC} = 0 to 2.1 V, V _O = 0.5 V to 2.7 V, OE = X [‡]			±50		±50		±50	μA
I _{OZPD}	V _{CC} = 2.1 V to 0, V _O = 0.5 V to 2.7 V, OE = X [‡]			±50		±50		±50	μA
I _{OZH}	V _{CC} = 2.1 V to 5.5 V, V _O = 2.7 V, OE ≤ 0.8 V			10		10		10	μA
I _{OZL}	V _{CC} = 2.1 V to 5.5 V, V _O = 0.5 V, OE ≤ 0.8 V			–10		–10		–10	μA
I _{off}	V _{CC} = 0, V _I or V _O ≤ 4.5 V			±100				±100	μA
I _{CEX}	V _{CC} = 5.5 V, V _O = 5.5 V, Outputs high			50		50		50	μA
I _{O§}	V _{CC} = 5.5 V, V _O = 2.5 V	–50	–100	–200	–50	–200	–50	–200	mA
I _{CC}	V _{CC} = 5.5 V, I _O = 0, V _I = V _{CC} or GND			1		250		250	μA
				24		30		30	mA
				0.5		250		250	μA
ΔI _{CC¶}	V _{CC} = 5.5 V, One input at 3.4 V, Other inputs at V _{CC} or GND			1.5		1.5		1.5	mA
				50		50		50	μA
C _i	V _I = 2.5 V or 0.5 V			3					pF
C _o	V _O = 2.5 V or 0.5 V			7					pF

* On products compliant to MIL-PRF-38535, this parameter does not apply.

† All typical values are at V_{CC} = 5 V.

‡ For V_{CC} between 2.1 V and 4 V, OE should be less than or equal to 0.5 V to ensure a low state.

§ Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

PRODUCT PREVIEW information concerns products in the formative or design phase of development. Characteristic data and other specifications are design goals. Texas Instruments reserves the right to change or discontinue these products without notice.



POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

SN54ABT126, SN74ABT126

QUADRUPLE BUS BUFFER GATES

WITH 3-STATE OUTPUTS

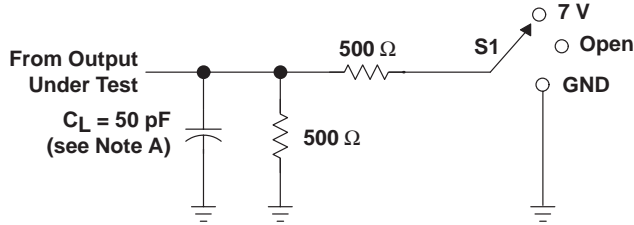
SCBS183D – FEBRUARY 1991 – REVISED JANUARY 1999

switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 1)

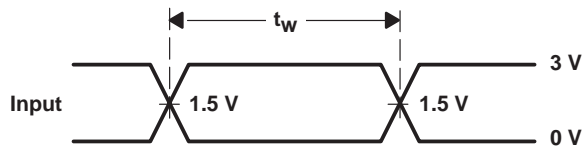
PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 5\text{ V},$ $T_A = 25^\circ\text{C}$			SN54ABT126		SN74ABT126		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A	Y	1	2.9	4.9	1	7.3	1	6.3	ns
t_{PHL}			1	2.5	5.1	1	5.9	1	5.7	
t_{PZH}	OE	Y	1	4.4	5.8	1	5.3	1	6.5	ns
t_{PZL}			1	4.4	5.9	1	6.4	1	6.5	
t_{PHZ}	OE	Y	1	3	5.7	1	6.9	1	6.8	ns
t_{PLZ}			1	3	5.8	1	7.2	1	6.7	

NOTE 4: Limits may vary among suppliers.

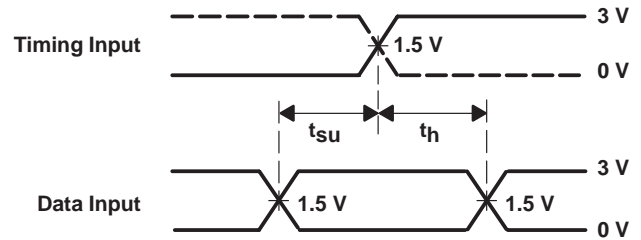
PARAMETER MEASUREMENT INFORMATION



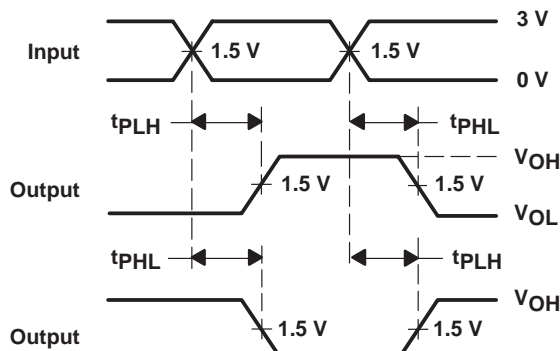
LOAD CIRCUIT



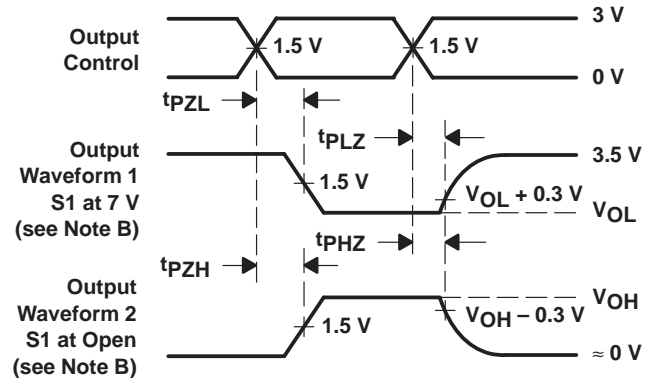
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

- NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r \leq 2.5 \text{ ns}$, $t_f \leq 2.5 \text{ ns}$.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.